

40V N-Channel Power SpeedFET
• General Description

It combines advanced trench MOSFET technology with a low resistance package to provide extremely low $R_{DS(ON)}$.

• Features

- Low $R_{DS(ON)}$ to minimize conductive loss
- Low Gate Charge for fast switching
- Low Thermal resistance

• Application

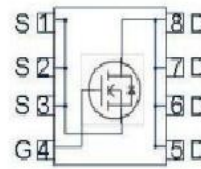
- BLDC Motor driver
- DC-DC
- Battery protection

• Ordering Information:

Part NO.	ZMS055N04HM
Marking	055N04H
Packing Information	REEL TAPE
Basic ordering unit (pcs)	5000

• Absolute Maximum Ratings ($T_C=25^\circ\text{C}$)

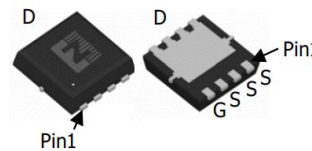
Parameter	Symbol	Conditions	Value	Unit
Drain-Source Voltage	V_{DS}	$25^\circ\text{C} \leq T_J \leq 175^\circ\text{C}$	40	V
Gate-Source Voltage ^①	V_{GS}		± 20	V
Continuous Drain Current	I_D	$T_C=25^\circ\text{C}$	48	A
	I_D	$T_C=75^\circ\text{C}$	42	A
	I_D	$T_C=100^\circ\text{C}$	33	A
Pulsed Drain Current	I_{DM}	Pulsed; $t_p \leq 10 \mu\text{s}$; $T_{mb} = 25^\circ\text{C}$;	192	A
Total Power Dissipation	P_D	$T_C=25^\circ\text{C}$	38	W
Total Power Dissipation	P_D	$T_A=25^\circ\text{C}$	2.5	W
Operating Junction Temperature	T_J		-55 to +175	$^\circ\text{C}$
Storage Temperature	T_{STG}		-55 to +175	$^\circ\text{C}$
Single Pulse Avalanche Energy	E_{AS}	$L=0.1\text{mH}$, $V_{GS}=10\text{V}$, $R_g=25\Omega$,	40	mJ
		$L=0.5\text{mH}$, $V_{GS}=10\text{V}$, $R_g=25\Omega$,	84	mJ
ESD Level (HBM)	CLASS 1C			

• Product Summary


$$V_{DS} = 40\text{V}$$

$$R_{DS(ON)} = 5.5\text{m}\Omega$$

$$I_D = 48\text{A}$$



DFN3*3



•Thermal resistance

Parameter	Symbol	Min.	Typ.	Max.	Unit
Thermal resistance, junction - case	RthJC		-	4.0	°C/W
Thermal resistance, junction-ambient	RthJA ^②		-	60	°C/W
Soldering temperature (total time<10s)	Tsold		-	260	°C

•Electronic Characteristics

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =250uA	40			V
Gate Threshold Voltage	V _{GS(TH)}	V _{GS} =V _{DS} , I _D =250uA	2.0	2.7	4.0	V
Drain-Source Leakage Current	I _{DSS}	V _{GS} =0V, V _{DS} = 40V			1.0	uA
Gate- Source Leakage Current	I _{GSS}	V _{GS} =±20V, V _{DS} = 0V			100	nA
Static Drain-source On Resistance	R _{DS(ON)}	V _{GS} =10V, I _D = 14A		5.5	7.1	mΩ
Forward Transconductance	g _{FS}	V _{GS} =5V, I _{SD} = 4A		7		s
Diode Forward Voltage	V _{FSD}	V _{GS} =0V, I _{SD} = 14A			1.3	V

•Dynamic characteristics

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Input capacitance	Ciss	f = 1MHz, V _{DS} =25V	-	908	-	pF
Output capacitance	Coss		-	244	-	
Reverse transfer capacitance	Crss		-	10	-	
Gate Resistance	Rg	f = 1MHz	-	1.2		Ω
Total gate charge	Qg	V _{DD} = 15V, I _D = 20A, V _{GS} = 10V	-	14	-	nC
Gate - Source charge	Qgs		-	3.2	-	
Gate - Drain charge	Qgd		-	3.5	-	
Turn-ON Delay time	t _{D(on)}	V _{GS} =10V, V _{DS} =15V, R _G =3.3Ω, I _D =20A	-	5	-	ns
Turn-ON Rise time	t _r		-	10	-	ns
Turn-Off Delay time	t _{D(off)}		-	24	-	ns
Turn-Off Fall time	t _f		-	8	-	ns
Reverse Recovery Time	t _{RR}	V _{DD} =20V, dI _S /dt = 100A/s, I _S =50A	-	30	-	ns
Reverse Recovery Charge	Q _{RR}		-	21	-	nC

Fig.1 Gate-Charge Characteristics

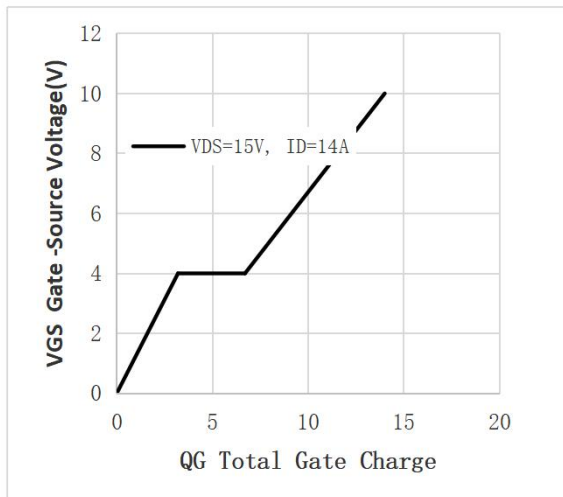


Fig.2 Capacitance Characteristics

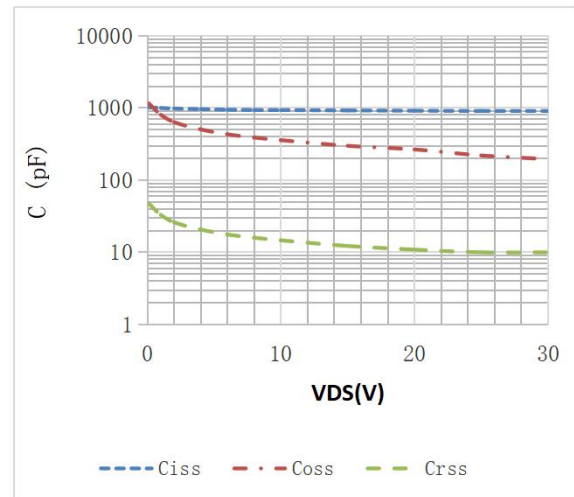


Fig.3 Power Dissipation

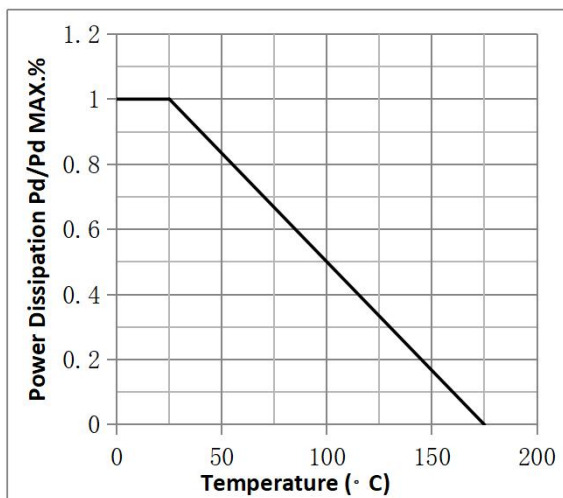


Fig.4 Typical output Characteristics

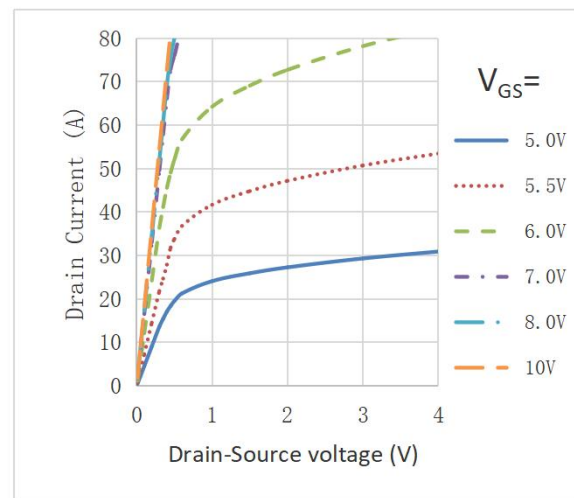


Fig.5 Threshold Voltage V.S Junction Temperature

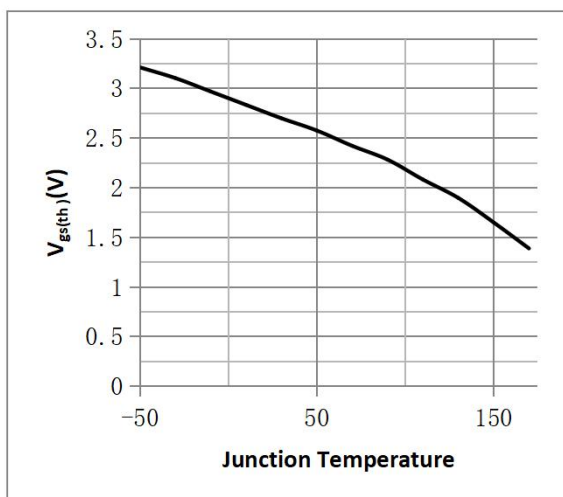


Fig.6 Resistance V.S Drain Current

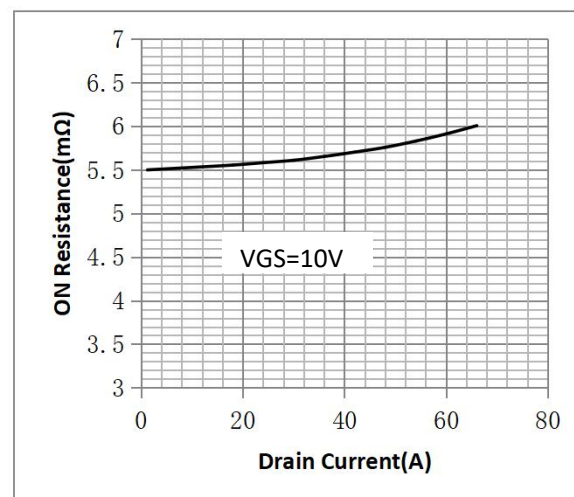


Fig.7 On-Resistance VS Gate Source Voltage

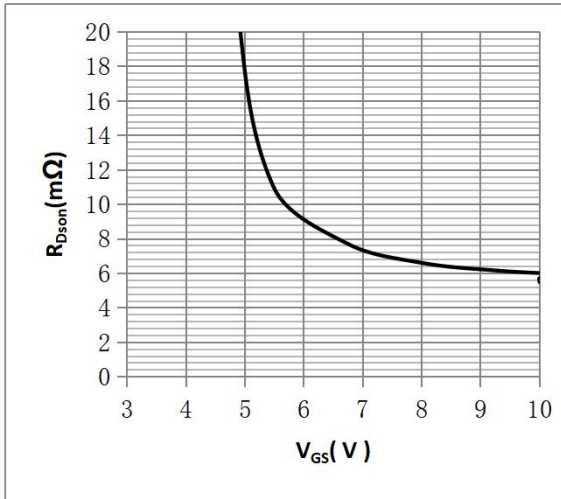


Fig.8 On-Resistance V.S Junction Temperature

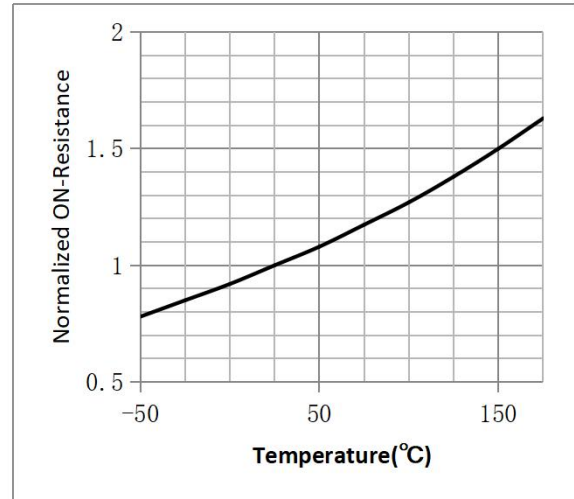


Figure 9. Diode Forward Voltage vs. Current

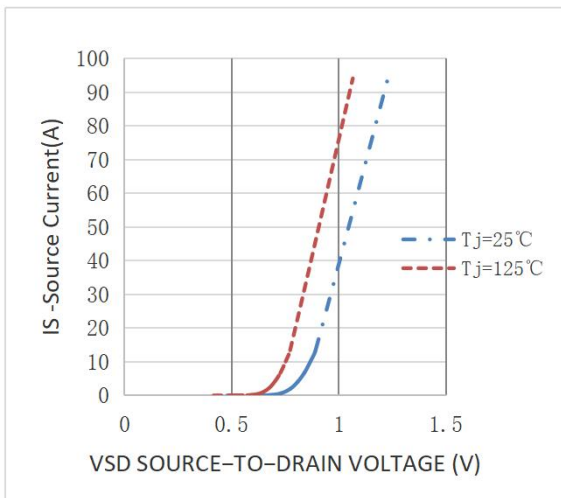


Figure 10. Transfer Characteristics

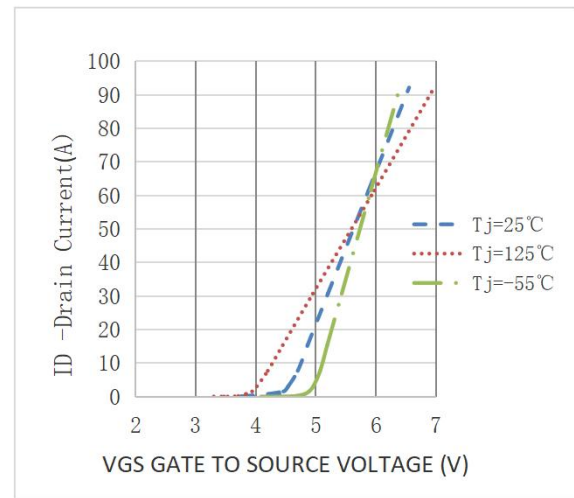


Fig.11 SOA Maximum Safe Operating Area

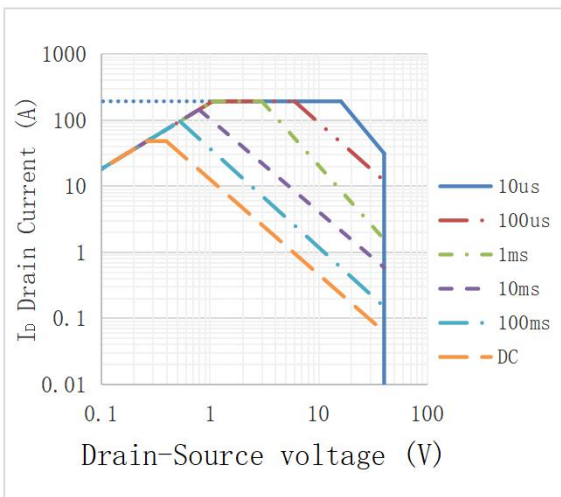
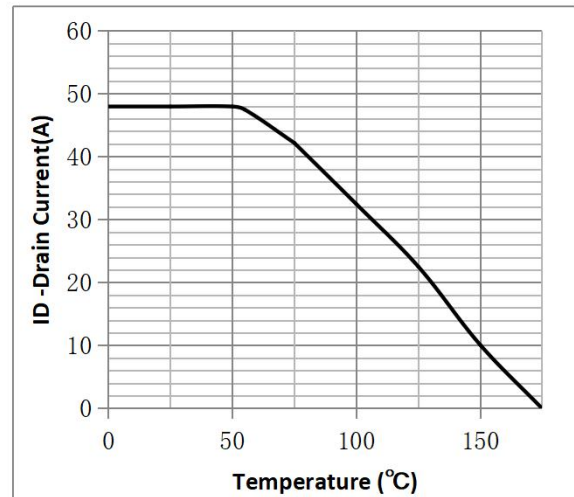
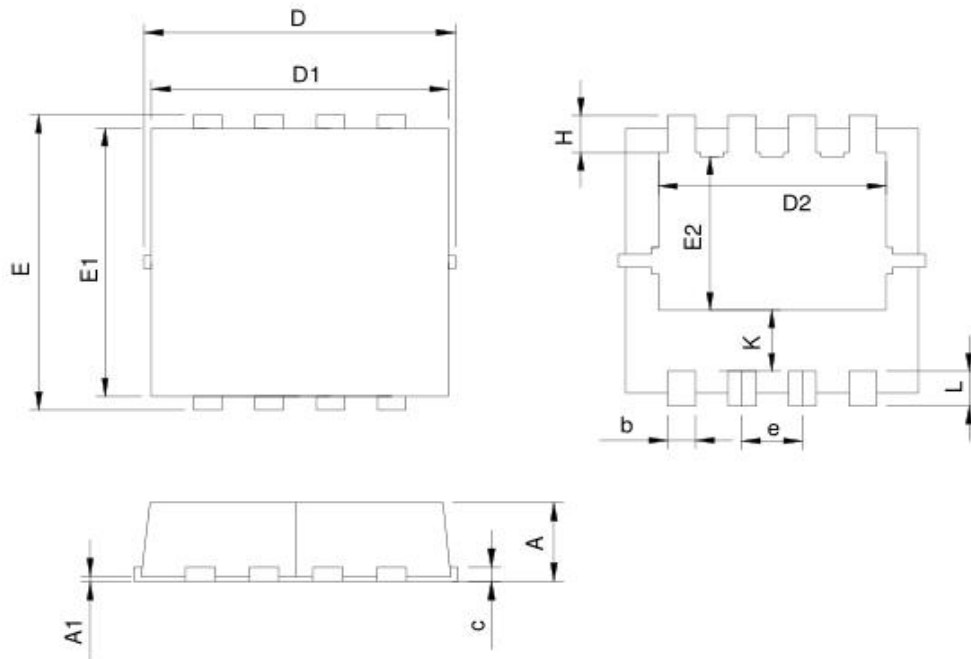


Fig.12 ID vs. Junction Temperature^③

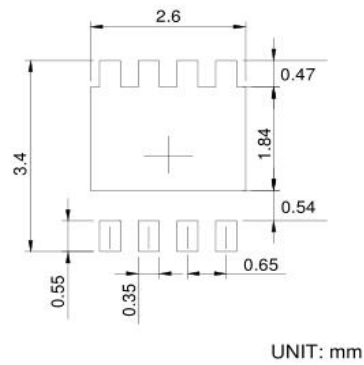


•DFN3*3 Package Outline



SYMBOL	DFN3.3x3.3-8			
	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	0.70	1.00	0.028	0.039
A1	0.00	0.05	0.000	0.002
b	0.25	0.35	0.010	0.014
c	0.14	0.20	0.006	0.008
D	3.10	3.50	0.122	0.138
D1	3.05	3.25	0.120	0.128
D2	2.35	2.55	0.093	0.100
E	3.10	3.50	0.122	0.138
E1	2.90	3.10	0.114	0.122
E2	1.64	1.84	0.065	0.072
e	0.65 BSC		0.026 BSC	
H	0.32	0.52	0.013	0.020
K	0.59	0.79	0.023	0.031
L	0.25	0.55	0.010	0.022

RECOMMENDED LAND PATTERN



UNIT: mm

Note:

- ① Pulse : $V_{GS}=+20V/-20V$, Duty cycle=50%, $T_j=175^{\circ}C$, $t=1000$ hours; For DC , the following test conditions can be passed: $V_{GS}=+20V/-10V$, $T_j=175^{\circ}C$, $t=1000$ hours;
- ② Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate;
- ③ Practically the current will be limited by PCB, thermal design and operating temperature. $V_{GS}=10V$.

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Revision History

Version	Date	Change
A	2022.1.6	
B	2022.2.26	1.Add Dynamic characteristic t_f , t_r etc.
C	2022.9.5	1.Add Reach, HF figure, 2.ID modify